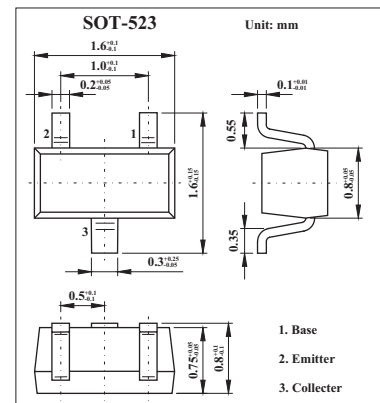


Switching Diode

BAS16T;BAW56T

BAV70T;BAV99T

■ Features

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

| Parameter | Symbol | Limits | Unit |
|--|-----------------------|-------------|------------------|
| Power dissipation ($T_{a\text{ mb}}=25^\circ\text{C}$) | P_D | 150 | mW |
| Forward Current | I_F | 75 | mA |
| Reverse Voltage | V_R | 85 | V |
| Operating and storage junction temperature range | T_J, T_{stg} | -55 to +150 | $^\circ\text{C}$ |

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

| Parameter | Symbol | Conditions | Min | Max | Unit |
|---------------------------------|------------|----------------------------------|-----|------|---------------|
| Reverse breakdown voltage | $V_{(BR)}$ | $I_R = 100\ \mu\text{A}$ | 85 | | V |
| Reverse voltage leakage current | I_R | $V_R = 75\ \text{V}$ | | 2 | μA |
| | | $V_R = 25\ \text{V}$ | | 0.03 | |
| Forward voltage | V_F | $I_F = 1\ \text{mA}$ | | 715 | mV |
| | | $I_F = 10\ \text{mA}$ | | 855 | |
| | | $I_F = 50\ \text{mA}$ | | 1000 | |
| | | $I_F = 150\ \text{mA}$ | | 1250 | |
| Diode capacitance | C_D | $V_R=0\ \text{V}, f=1\text{MHz}$ | | 1.5 | pF |
| Reverse recovery time | t_{rr} | | | 4 | ns |

■ Marking

| Type | BAS16T | BAW56T | BAV70T | BAV99T |
|---------|--------|--------|--------|--------|
| Marking | A2 | JD | JJ | JE |